T.4-52011.011 01-0.0072dd13

Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4.5	kV

(T_j=25 unless otherwise specified) **q EMC /P <</MCI3.6 7 >>**

FIG.1: Maximum power dissipation versus RMS on-state current

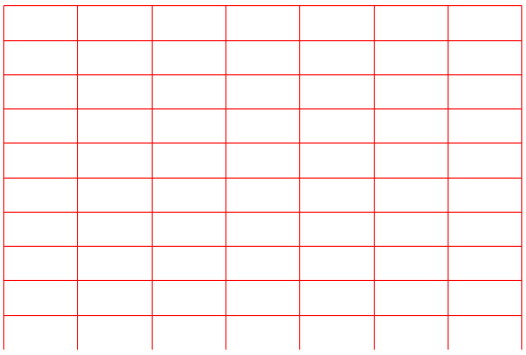
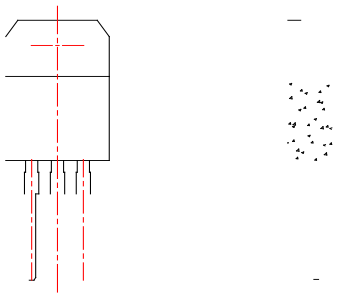


FIG.2: RMS on-state current versus case temperature

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
T1250H-6A	600	50	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated



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